

**isc Silicon PNP Transistor**

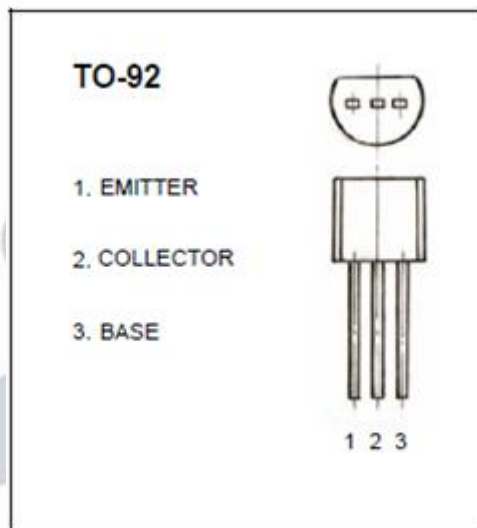
**2SA1283**

**DESCRIPTION**

- High Voltage and High Current  
V<sub>ceo</sub>=-60V(Min.)
- Excellent hFE Linearity
- Low Noise
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Audio frequency general purpose amplifier Applications
- Driver stage amplifier applications.



**ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)**

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	-60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-60	V
V <sub>EBO</sub>	Emitter-Base Voltage	-6	V
I <sub>C</sub>	Collector Curren	-1	A
P <sub>C</sub>	Collector Power Dissipation @T <sub>c</sub> =25°C	900	mW
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C

**isc Silicon PNP Transistor****2SA1283****ELECTRICAL CHARACTERISTICS** $T_c=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -500\text{mA}$ ; $I_B = -25\text{mA}$			-0.3	V
$I_{CBO}$	Emitter Cutoff Current	$V_{CB} = -50\text{V}$ ; $I_E = 0$			-0.2	$\mu\text{A}$
$I_{EBO}$	Collector Cutoff Current	$V_{EB} = -4\text{V}$ ; $I_C = 0$			-0.2	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$I_C = -100\text{mA}$ ; $V_{CE} = -4\text{V}$	55		300	

◆  **$h_{FE}$  Classifications**

C	D	E
55-110	90-180	150-300